

DUAL LOW-NOISE J-FET INPUT OPERATIONAL AMPLIFIERS

DESCRIPTION

The M5238 is a semiconductor integrated circuit designed as a low-noise Bi-FET operational amplifier which adopts J-FETs in the input stage. Noise reduction characteristic in the input stage has been improved by 3 - 4dB, when compared with the M5221 general-purpose Bi-FET operational amplifier, and two circuits for yielding a high input impedance, high slew rate and low bias current and other excellent characteristics, are housed in an 8-pin SIP, DIP or FP.

It can be widely used as a general-purpose operational amplifier in stereo equipment, tape decks, digital audio disc players and other similar products as well as in VCRs, video disc players and video related players.

FEATURES

- Low noise, input-referred noise $V_{NI} = 1.9 \mu\text{Vrms}$ (typ.)
($R_s = 100\text{k}\Omega$ BW10Hz~30kHz FLAT)
 $S/N = 73\text{dB}$ (typ.)
(Shorted input, RIAA, IHF-A network, PHONO 2.5mVrms)
- High input impedance due to J-FET input $R_i = 1000\text{M}\Omega$ (typ.)
- High slew rate $S_R = 20\text{V}/\mu\text{s}$ (typ.)
- High gain, low distortion $G_v = 100\text{dB}$ (typ.), THD = 0.002%
($G_v = 35.6\text{dB}$, RIAA, $V_o = 5\text{Vrms}$)
- Large load current and allowable current $I_{LP} = \pm 50\text{mA}$, $P_d = 800\text{mW}$ (SIP)
 $P_d = 625\text{mW}$ (DIP), $P_d = 440\text{mW}$ (FP)

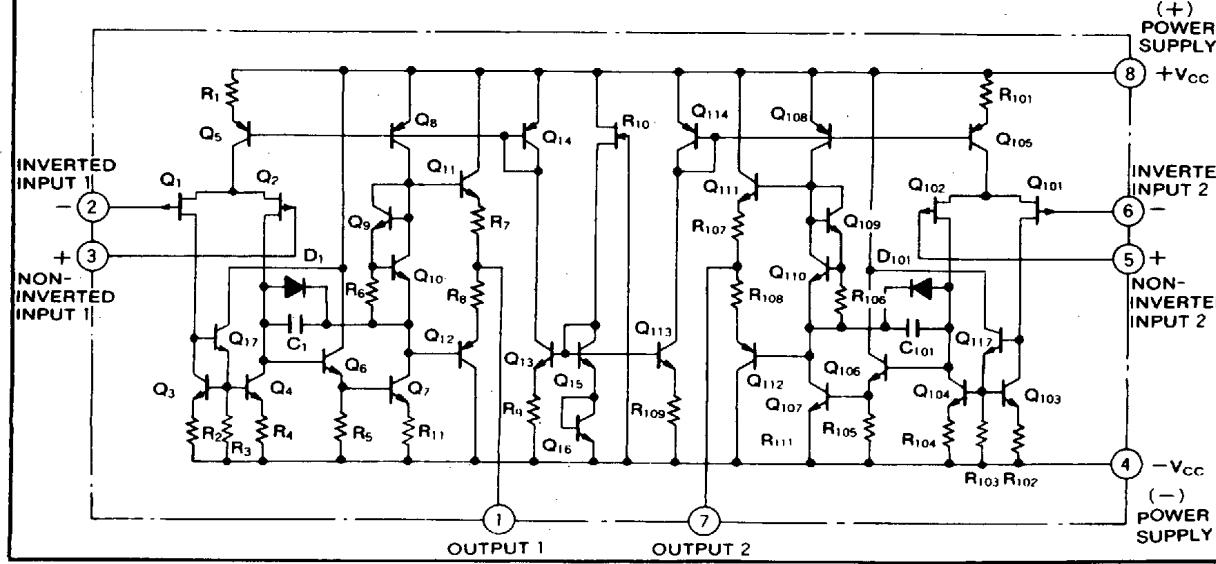
APPLICATION

General purpose preamplifier in stereo equipment, tape decks and digital audio disc players, VCRs and video disc players.

RECOMMENDED OPERATING CONDITION

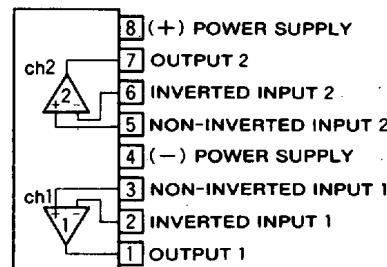
- Supply voltage range $\pm 5 \sim \pm 15\text{V}$
- Rated supply voltage $\pm 15\text{V}$

BLOCK DIAGRAM

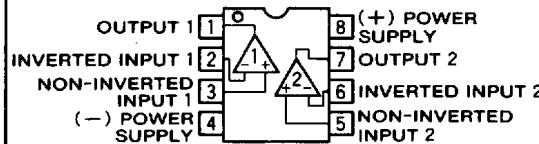


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PIN CONFIGURATION (TOP VIEW)



Outline 8P5 (AL)

Outline 8P4 (AP)
8P2S-A (AFP)

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ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$, unless otherwise noted)

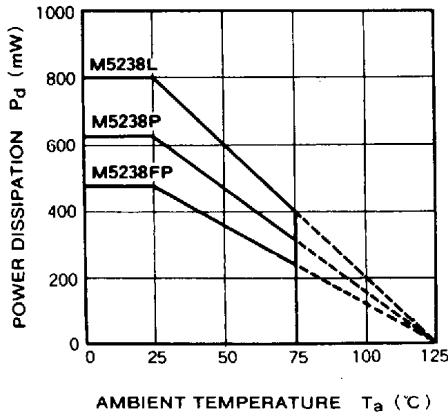
Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply voltage		± 18	V
I_{LP}	Load current		± 50	mA
V_{id}	Differential input voltage		± 30	V
V_{ic}	Common input voltage		± 15	V
P_d	Power dissipation		800(SIP)/625(DIP)/440(FP)	mW
K_θ	Thermal derating	$T_a \geq 25^\circ\text{C}$	8(SIP)/6.25(DIP)/4.4(FP)	mW/°C
T_{opr}	Ambient temperature		-20 ~ +75	°C
T_{stg}	Storage temperature		-55 ~ +125	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$, $V_{CC}=\pm 15\text{V}$)

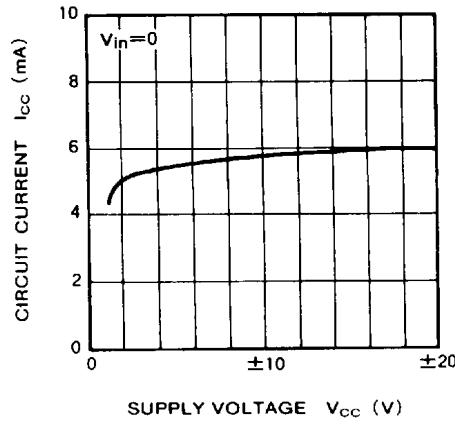
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{CC}	Circuit current	$V_{in}=0$		5.8	9.0	mA
V_{IO}	Input offset voltage	$R_s \leq 10\text{k}\Omega$		2.0	10.0	mV
I_{IO}	Input offset current			5	200	pA
I_B	Input bias current			30	400	pA
R_{in}	Input resistance			10^3		MΩ
G_{vo}	Open loop voltage gain	$R_L \geq 2\text{k}\Omega, V_o = \pm 10\text{V}$	86	106		dB
V_{OM}	Maximum output voltage	$R_L \geq 10\text{k}\Omega$	± 12	± 14		V
		$R_L \geq 2\text{k}\Omega$	± 10	± 13		
V_{CM}	Common input voltage width		± 10	± 12		V
CMRR	Common mode rejection ratio	$R_s \leq 10\text{k}\Omega$	70	76		dB
SVRR	Supply voltage rejection ratio	$R_s \leq 10\text{k}\Omega$		30	150	$\mu\text{V}/\text{V}$
P_d	Power dissipation			174	270	mW
SR	Slew rate	$G_V=0\text{dB}, R_L=2\text{k}\Omega$		20		$\text{V}/\mu\text{s}$
f_T	Gain bandwidth product			6		MHz
V_{NI}	Input referred noise voltage	$R_s=100\Omega, BW=10\text{Hz} \sim 30\text{kHz}$		1.9		μVRms

TYPICAL CHARACTERISTICS

THERMAL DERATING (MAXIMUM RATING)



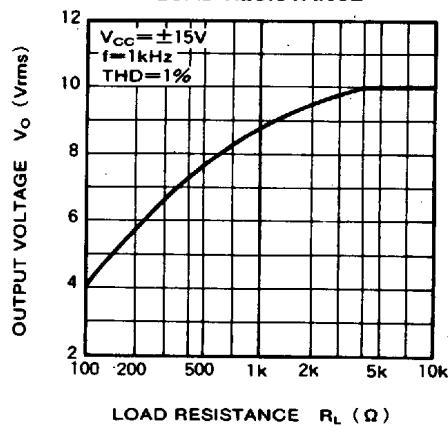
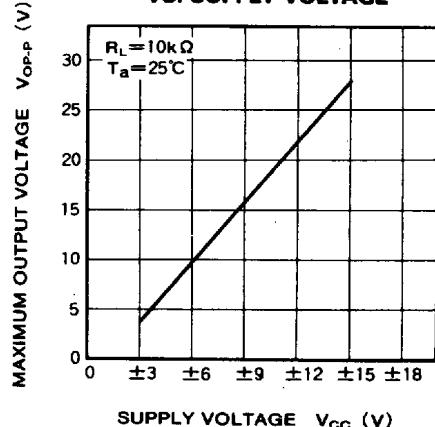
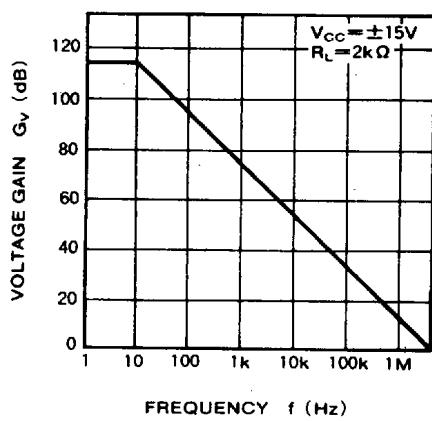
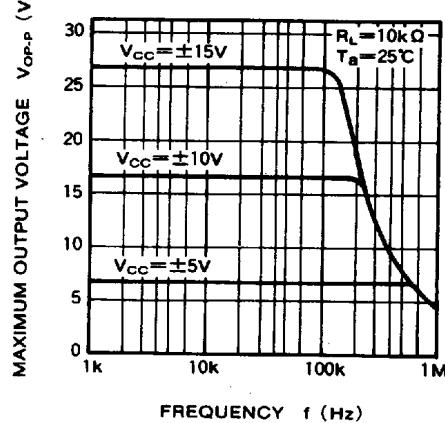
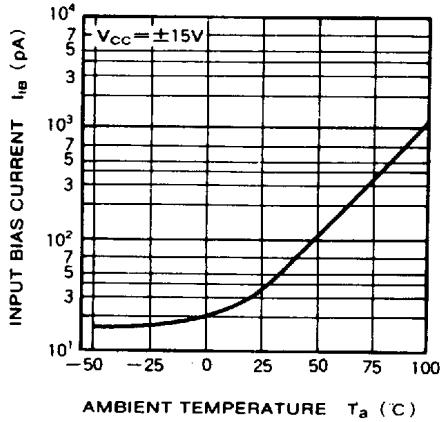
**CIRCUIT CURRENT VS.
SUPPLY VOLTAGE**



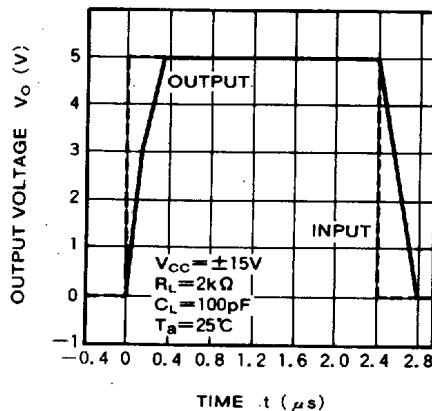
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OUTPUT VOLTAGE VS.
LOAD RESISTANCEMAXIMUM OUTPUT VOLTAGE
VS. SUPPLY VOLTAGEVOLTAGE GAIN VS.
FREQUENCY RESPONSEMAXIMUM OUTPUT
VOLTAGE VS. FREQUENCYINPUT BIAS CURRENT VS.
AMBIENT TEMPERATURE

SLEW RATE (SR) CHARACTERISTICS



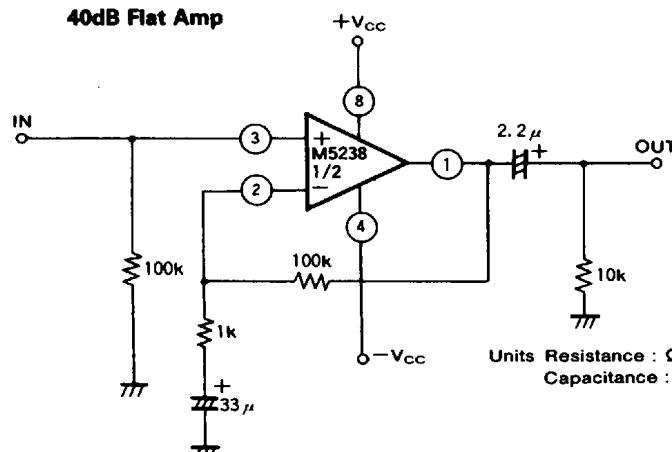
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DUAL LOW-NOISE J-FET INPUT OPERATIONAL AMPLIFIERS

APPLICATION CIRCUIT 1

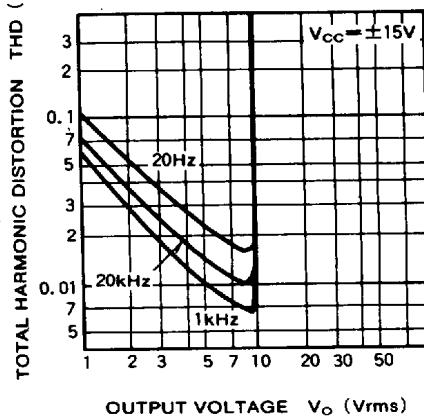
40dB Flat Amp



TYPICAL CHARACTERISTICS

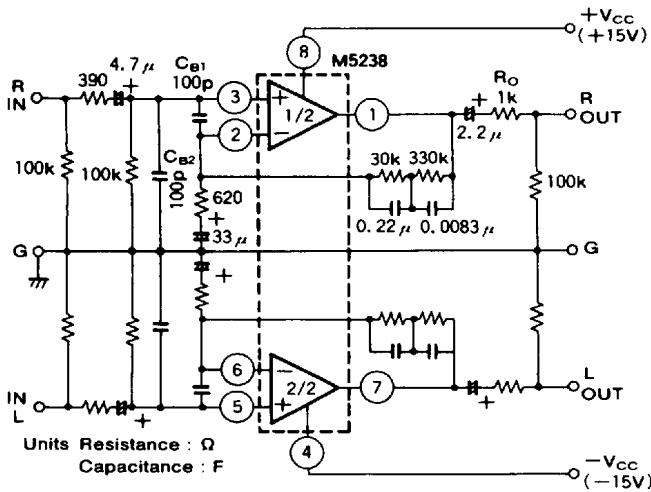
- $V_{CC} = \pm 15V$
- $G_v = 40dB (f = 1kHz)$
- $V_o = 9.5Vrms (f = 1kHz, THD = 0.1\%)$
- $THD = 0.007\% (f = 1kHz, V_o = 7Vrms)$

TOTAL HARMONIC DISTORTION VS. OUTPUT VOLTAGE



APPLICATION CIRCUIT 2

Stereo equalizer amplifier circuit



Lch circuit constants are identical to those of Rch.

C_{B1}, C_{B2} : Capacitors for buzz prevention, use if required.

R_O : Resistor used to prevent parasitic oscillation for capacitive loads and current limiting with shorted and other abnormal load conditions.

TYPICAL CHARACTERISTICS ($V_{CC} = \pm 15V$, RIAA)

- $G_v = 35.6dB (f = 1kHz)$
- $V_{NI} = 1.9\mu Vrms (R_s = 100\Omega, BW = 20Hz \sim 30kHz)$
- $S/N = 73dB$ (IHF-A network, shorted input, 2.5mVrms input sensitivity)
- $THD = 0.001\% (f = 1kHz, V_o = 7Vrms)$

TOTAL HARMONIC DISTORTION VS. OUTPUT VOLTAGE

